## IV B.Tech I Semester Supplementary Examinations, March - 2017 VLSI DESIGN

(Common to Electronics & Communication Engineering, and Electronics & Instumentation Engineering)

Time: 3 hours Max. Marks: 70 Question paper consists of Part-A and Part-B Answer ALL sub questions from Part-A Answer any THREE questions from Part-B \*\*\*\* PART-A (22 Marks) 1. a) Write down the equations  $\overline{\text{for } I_{ds} \text{ of }}$  an n-channel enhancement MOSFET operating in Non-saturated region and saturated region? [4] Define stick diagram and layout diagram? [4] b) Explain about the constraints in choice of layers. [4] Draw the basic structure of a dynamic CMOS gate? d) [4] List out the back-end steps in ASIC design flow? [3] List out the front-end steps in FPGA design flow? f) [3] PART-B (3x16 = 48 Marks)Explain the nMOS enhancement mode fabrication process for different 2. a) conditions of V<sub>ds</sub>? [8] Derive an equation for transconductance of an n-channel enhancement MOSFET operating in active region. [8] 3. a) Design a stick diagram and layout for two input CMOS NAND gate indicating all the regions and layers. [8] b) Explain 2µm Double Metal, Double Poly. CMOS / BiCMOS Rules. [8] 4. What are the issues involved in driving large capacitor loads in VLSI circuit a) regions? Explain. [8] b) Calculate the gate capacitance value of 5mm technology minimum size transistor with gate to channel value is  $4 \times 10^{-4} \text{ pF/mm}^2$ . [8] How switch logic can be implemented using Pass Transistors? Explain. 5. a) [8] Draw the transistor circuit diagram of shift register capable of holding and shifting 4-bit word. Explain the circuit operation. [8] 6. a) What are FPGAs? Explain the principle and operation. [8] Explain how the pass transistors are used to connect wire segments for the b) purpose of FPGA programming. [8] 7. a) Clearly explain each step of high level design flow of an ASIC. [8] b) Write a short note on mixed signal design? [8]

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